查询GT20D201供应商 捷多邦，专业PCB打样工厂，24小时加急出货

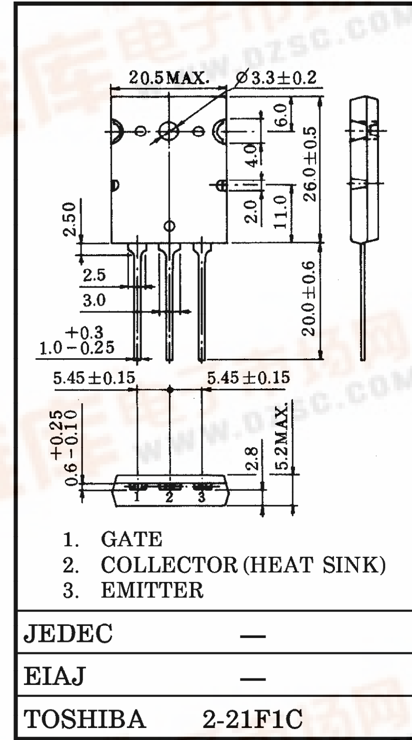
TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON P CHANNEL TYPE

GT20D201

HIGH POWER AMPLIFIER APPLICATION

- High Breakdown Voltage : $V_{CES} = -250V$ (Min.)
- High Forward Transfer Admittance : $|Y_{fe}| = 10S$ (Typ.)
- Complementary to GT20D101
- Enhancement-Mode

Unit in mm



1. GATE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC	—
EIAJ	—
TOSHIBA	2-21F1C

Weight : 9.75g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CES}	−250	V
Gate-Emitter Voltage	V_{GES}	±20	V
Collector Current	I_C	−20	A
Latch Up Current	I_L	−60	A
Collector Power Dissipation (Tc = 25°C)	P_C	180	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CES}	$V_{CE} = -250V$, $V_{GE} = 0$	—	—	−50	μA
Gate Leakage Current	I_{GES}	$V_{GE} = \pm20V$, $V_{CE} = 0$	—	—	±10	μA
Collector-Emitter Saturation Voltage	$V_{CE\ (sat)}$	$I_C = -15A$, $V_{GE} = -10V$	—	−1.7	−3.0	V
Gate-Emitter Cut-off Voltage	$V_{GE\ (OFF)}$	$V_{CE} = -10V$, $I_C = -100mA$	−1.4	—	−3.2	V
Forward Transfer Admittance	$\lvert Y_{fe} \rvert$	$V_{CE} = -10V$, $I_C = -1A$	—	3	—	S
	$\lvert Y_{fe} \rvert$	$V_{CE} = -10V$, $I_C = -10A$	—	10	—	
Input Capacitance	C_{ies}	$V_{CE} = -10V$, $I_E = 0$, f = 1MHz	—	1450	—	pF
Output Capacitance	C_{oes}	$V_{CE} = -10V$, $I_E = 0$, f = 1MHz	—	450	—	pF
Reverse Transfer Capacitance	C_{res}	$V_{CE} = -10V$, $I_E = 0$, f = 1MHz	—	50	—	pF

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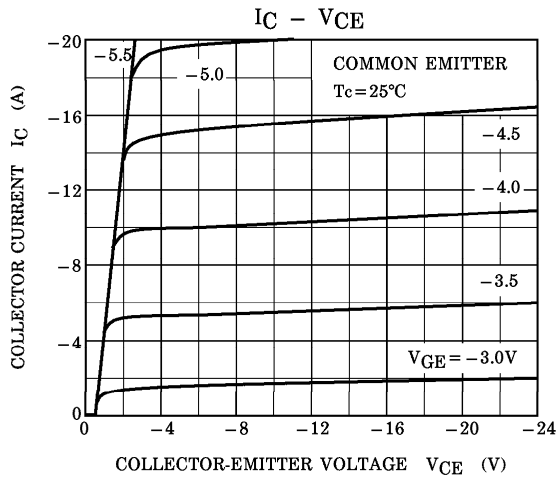

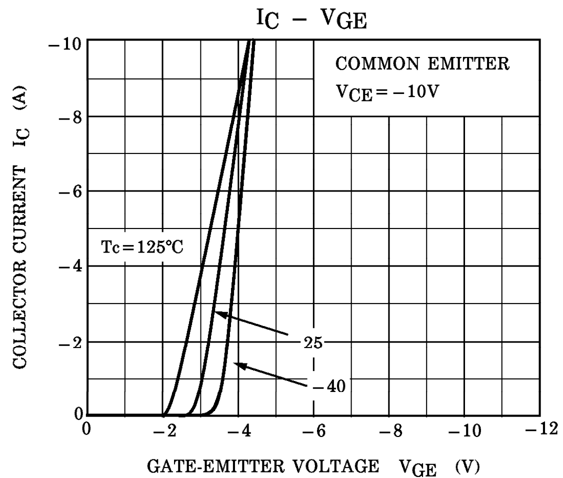

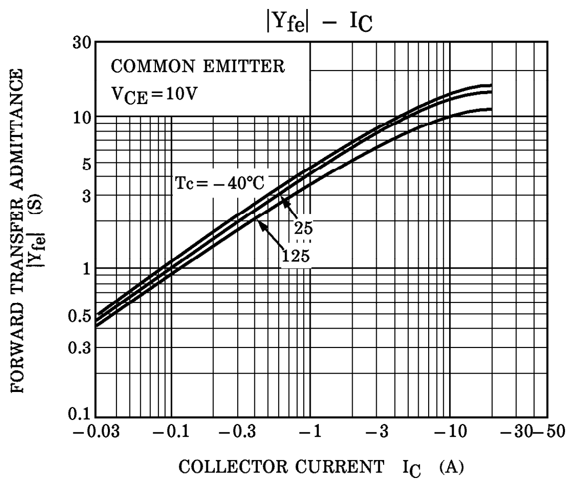

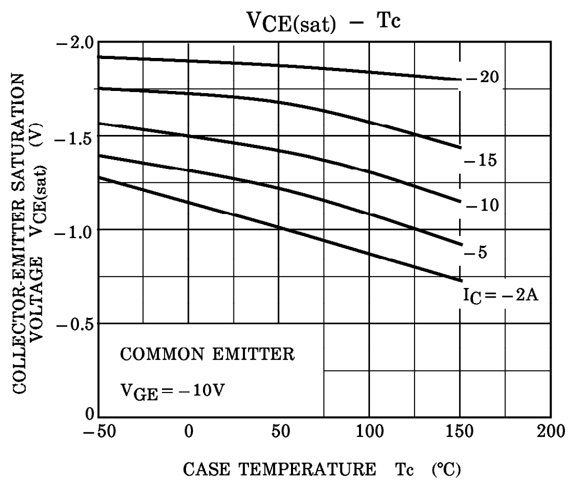

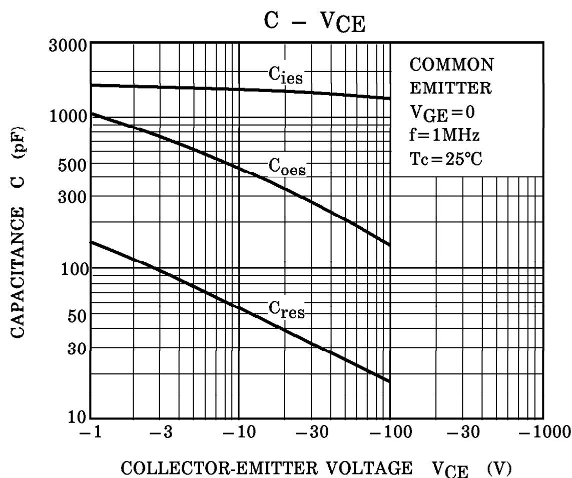

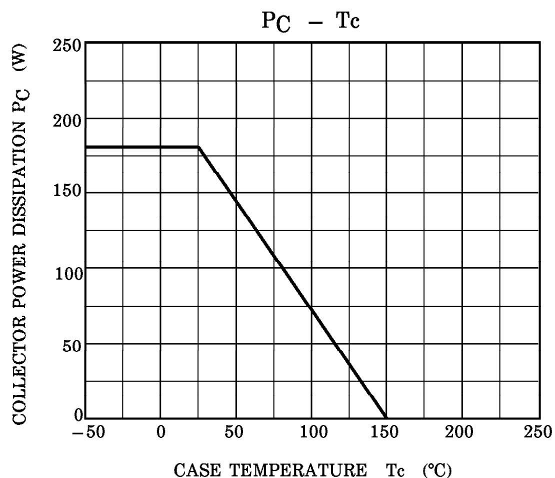

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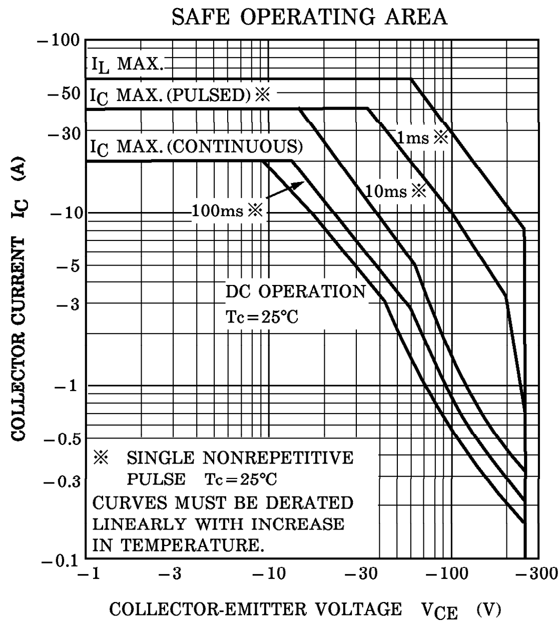
SAFE OPERATING AREA
I_L MAX.
I_C MAX. (PULSED) ※
I_C MAX. (CONTINUOUS)
1ms ※
10ms ※
100ms ※
DC OPERATION
Tc = 25°C
※ SINGLE NONREPETITIVE PULSE Tc = 25°C
CURVES MUST BE DERATED LINEARLY WITH INCREASE IN TEMPERATURE.
−100
−50
−30
−10
−5
−3
−1
−0.5
−0.3
−0.1
−1
−3
−10
−30
−100
−300
COLLECTOR CURRENT I_C (A)
COLLECTOR-EMITTER VOLTAGE V_{CE} (V)